

# CMOS Low Voltage 2.5 Ω Dual SPDT Switch

## ADG736L

### **FEATURES**

1.8 V to 5.5 V single supply 2.5  $\Omega$  (typical) on resistance Low on-resistance flatness Guaranteed leakage performance over -40°C to +85°C -3 dB bandwidth > 200 MHz Rail-to-rail operation 10-lead MSOP package Fast switching times ton 16 ns toFF 8 ns Typical power consumption (<0.01  $\mu$ W) TTL/CMOS compatible

### **APPLICATIONS**

USB 1.1 signal switching circuits Cell phones PDAs Battery-powered systems Communication systems Sample-and-hold systems Audio signal routing Audio and video switching Mechanical reed relay replacement

### **GENERAL DESCRIPTION**

The ADG736L is a monolithic device comprising two independently selectable CMOS single pole, double throw (SPDT) switches. The switches are designed using a submicron process that provides low power dissipation, yet gives high switching speed, low on resistance, low leakage currents, and wide input signal bandwidth.

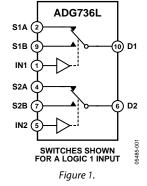
The on resistance profile is very flat over the full analog signal range. This ensures excellent linearity and low distortion when switching audio signals. Fast switching speed also makes the part suitable for video signal switching.

The ADG736L operates from a single 1.8 V to 5.5 V supply, making it ideally suited to portable and battery-powered instruments.

Each switch conducts equally well in both directions when on; each has an input signal range that extends to the power supplies. The ADG736L exhibits break-before-make switching action.

The ADG736L is available in a 10-lead MSOP.

### FUNCTIONAL BLOCK DIAGRAM



### **PRODUCT HIGHLIGHTS**

- 1. 1.8 V to 5.5 V Single-Supply Operation.
- 2. Guaranteed Leakage Performance.
- 3. Very Low  $R_{ON}$  (4.5  $\Omega$  Maximum at 5 V, 8  $\Omega$  Maximum at 3 V).
- 4. Low On Resistance Flatness.
- 5. -3 dB Bandwidth > 200 MHz.
- 6. Low Power Dissipation.

#### Rev. 0

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### **REVISION HISTORY**

1/07—Revision 0: Initial Version

### **SPECIFICATIONS**

 $V_{\text{DD}}$  = 5 V  $\pm$  10%, GND = 0 V; all specifications –40°C to +85°C, unless otherwise noted.

### Table 1.

	B Version <sup>1</sup>				
Demonstern	2585	-40°C to	1114		
Parameter ANALOG SWITCH	25°C	+85°C	Unit	Test Conditions/Comments	
		0 V to V	v		
Analog Signal Range On Resistance (R <sub>oN</sub> )	2.5	0 V to V <sub>DD</sub>	v Ω typ	$V_s = 0 V$ to $V_{DD}$ , $I_{DS} = -10 \text{ mA}$ ; see Figure 10	
On Resistance (RON)	4	4.5		$v_s = 0$ v to $v_{DD}$ , $I_{Ds} = -10$ mA; see Figure 10	
On Desisten as Match Patruson Channels (AD.)		4.5	Ω max		
On Resistance Match Between Channels ( $\Delta R_{ON}$ )	0.1		Ω typ	$V_{s} = 0 V$ to $V_{DD}$ , $I_{Ds} = -10 \text{ mA}$	
		0.4	Ωmax		
On Resistance Flatness (R <sub>FLAT (ON)</sub> )	0.5		Ωtyp	$V_{\rm S} = 0$ V to $V_{\rm DD}$ , $I_{\rm DS} = -10$ mA	
		1.2	Ωmax		
LEAKAGE CURRENTS				$V_{DD} = 5.5 V$	
Source Off Leakage Is (OFF)	±0.01		nA typ	$V_{S} = 4.5 \text{ V}/1 \text{ V}, V_{D} = 1 \text{ V}/4.5 \text{ V};$ see Figure 11	
	±0.1	±0.3	nA max		
Channel On Leakage I <sub>D</sub> , I <sub>s</sub> (ON)	±0.01		nA typ	$V_s = V_D = 1 V \text{ or } 4.5 V$ ; see Figure 12	
	±0.1	±0.3	nA max		
DIGITAL INPUTS					
Input High Voltage, V <sub>INH</sub>		2.4	V min		
Input Low Voltage, VINL		0.8	V max		
Input Current, IINL or IINH					
	0.005		μA typ	$V_{\text{IN}} = V_{\text{INL}} \text{ or } V_{\text{INH}}$	
		±0.1	µA max		
DYNAMIC CHARACTERISTICS <sup>2</sup>					
ton	12		ns typ	$R_L = 300 \ \Omega$ , $C_L = 35 \ pF$	
		16	ns max	$V_s = 3 V$ ; see Figure 13	
t <sub>OFF</sub>	5		ns typ	$R_L=300~\Omega,~C_L=35~pF$	
		8	ns max	$V_s = 3 V$ ; see Figure 13	
Break-Before-Make Time Delay, t <sub>D</sub>	7		ns typ	$R_L = 300 \ \Omega$ , $C_L = 35 \ pF$	
		1	ns min	$V_{S1} = V_{S2} = 3 V$ ; see Figure 14	
Off Isolation	-62		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 10 MHz$	
	-82		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 15	
Channel-to-Channel Crosstalk	-62		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 10 MHz$	
	-82		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 16	
Bandwidth (–3 dB)	200		MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ ; see Figure 17	
C <sub>s</sub> (OFF)	9		pF typ		
C <sub>D</sub> , C <sub>S</sub> (ON)	32		pF typ		
POWER REQUIREMENTS			1	$V_{DD} = 5.5 V$	
	0.001		μA typ	Digital inputs = $0 \text{ V}$ or $5 \text{ V}$	
		1.0	μA max		

 $^1$  Temperature range is  $-40^\circ C$  to  $+85^\circ C$  for the B version.  $^2$  Guaranteed by design; not subject to production test.

 $V_{DD}$  = 3 V ± 10%, GND = 0 V. All specifications –40°C to +85°C, unless otherwise noted.

### Table 2.

	B Version <sup>1</sup>				
_		-40°C to	]		
Parameter	25°C	+85°C	Unit	Test Conditions/Comments	
ANALOG SWITCH					
Analog Signal Range		0 V to V <sub>DD</sub>	V		
On Resistance (R <sub>on</sub> )	5	5.5	Ωtyp	$V_{s} = 0 V$ to $V_{DD}$ , $I_{DS} = -10 \text{ mA}$ ; see Figure 10	
		8	Ωmax		
On Resistance Match Between Channels ( $\Delta R_{ON}$ )	0.1		Ωtyp	$V_{s} = 0 V$ to $V_{DD}$ , $I_{DS} = -10 \text{ mA}$	
		0.4	Ωmax		
On Resistance Flatness (R <sub>FLAT (ON)</sub> )		2.5	Ωtyp	$V_s = 0 V$ to $V_{DD}$ , $I_{Ds} = -10 \text{ mA}$	
LEAKAGE CURRENTS				$V_{DD} = 3.3 V$	
Source Off Leakage Is (OFF)	±0.01		nA typ	$V_{\text{S}}$ = 3 V/1 V, $V_{\text{D}}$ = 1 V/3 V; see Figure 11	
	±0.1	±0.3	nA max		
Channel On Leakage I <sub>D</sub> , Is (ON)	±0.01		nA typ	$V_s = V_D = 1 V \text{ or } 3 V$ ; see Figure 12	
	±0.1	±0.3	nA max		
DIGITAL INPUTS					
Input High Voltage, V <sub>INH</sub>		2.0	V min		
Input Low Voltage, VINL		0.4	V max		
Input Current, I <sub>INL</sub> or I <sub>INH</sub>					
	0.005		μA typ	$V_{\text{IN}} = V_{\text{INL}} \text{ or } V_{\text{INH}}$	
		±0.1	μA max		
DYNAMIC CHARACTERISTICS <sup>2</sup>					
ton	14		ns typ	$R_L = 300 \ \Omega$ , $C_L = 35 \ pF$	
		20	ns max	$V_s = 2 V$ ; see Figure 13	
toff	6		ns typ	$R_L=300~\Omega,C_L=35~pF$	
		10	ns max	Vs = 2 V; see Figure 13	
Break-Before-Make Time Delay, t <sub>D</sub>	7		ns typ	$R_L = 300 \Omega$ , $C_L = 35 pF$	
		1	ns min	$V_{51} = V_{52} = 2 V$ ; see Figure 14	
Off Isolation	-62		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 10 MHz$	
	-82		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 15	
Channel-to-Channel Crosstalk	-62		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 10 MHz$	
enanner to enanner crosstark	-82		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; see Figure 16	
Bandwidth (–3 dB)	200		MHz typ	$R_L = 50 \Omega_2$ , $C_L = 5 pF$ ; $r = 1 m R_2$ , see Figure 17 $R_L = 50 \Omega_2$ , $C_L = 5 pF$ ; see Figure 17	
$C_{s}$ (OFF)	9		pF typ	$m_{\rm L} = 50.22, c_{\rm L} = 5.01, see Figure 17$	
C <sub>5</sub> (OFF) C <sub>D</sub> , C <sub>5</sub> (ON)	32		pF typ pF typ		
POWER REQUIREMENTS	52		pi typ	V <sub>DD</sub> = 3.3 V	
	0.001			Digital inputs = $0 \text{ V} \text{ or } 3 \text{ V}$	
I <sub>DD</sub>	0.001	1.0	μA typ μA max		

 $^1$  Temperature range is  $-40^\circ\text{C}$  to  $+85^\circ\text{C}$  for the B version.  $^2$  Guaranteed by design; not subject to production test.

### ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}C$ , unless otherwise noted.

#### Table 3.

Parameter	Rating
V <sub>DD</sub> to GND	-0.3 V to +6 V
Analog, Digital Inputs <sup>1</sup>	–0.3 V to $V_{DD}$ + 0.3 V or 30 mA, whichever occurs first
Continuous Current, S or D	30 mA
Peak Current, S or D	100 mA (Pulsed at 1 ms, 10% duty cycle maximum)
Operating Temperature Range	
Industrial (B Version)	–40°C to +85°C
Storage Temperature Range	–65°C to +150°C
Junction Temperature	150°C
MSOP Package, Power Dissipation	315 mW
$\theta_{JA}$ Thermal Impedance	205°C/W
Lead Temperature (Soldering, 10 sec)	300°C
IR Reflow (Peak Temperature, <20 sec)	235°C
Lead-Free Reflow	
Peak Temperature	260(+0/-5)°C
Time at Peak Temperature	10 sec to 40 sec
ESD	2 kV

<sup>1</sup> Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Only one absolute maximum rating may be applied at any one time.

### **ESD CAUTION**



**ESD** (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

### **PIN CONFIGURATION AND FUNCTION DESCRIPTIONS**

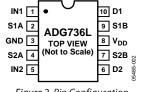


Figure 2. Pin Configuration

#### **Table 4. Pin Function Descriptions**

Pin No.	Mnemonic	Description
1	IN1	Logic Control Input.
2	S1A	Source Terminal. May be an input or an output.
3	GND	Ground (0 V) Reference.
4	S2A	Source Terminal. May be an input or an output.
5	IN2	Logic Control Input.
6	D2	Drain Terminal. May be an input or an output.
7	S2B	Source Terminal. May be an input or an output.
8	V <sub>DD</sub>	Most Positive Power Supply Potential.
9	S1B	Source Terminal. May be an input or an output.
10	D1	Drain Terminal. May be an input or an output.

#### Table 5. Truth Table

Logic	Switch A	Switch B
0	Off	On
1	On	Off

### **TYPICAL PERFORMANCE CHARACTERISTICS**

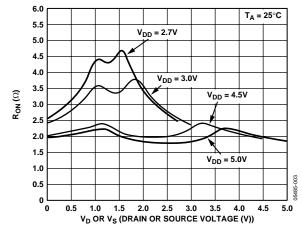


Figure 3. On Resistance as a Function of  $V_D$  ( $V_S$ ) Single Supplies

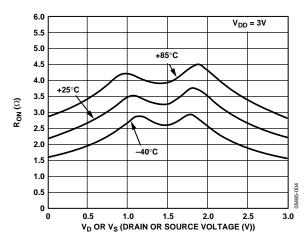


Figure 4. On Resistance as a Function of  $V_{\text{D}}$  (V\_{\text{S}}) for Different Temperatures  $V_{\text{DD}}$  = 3 V

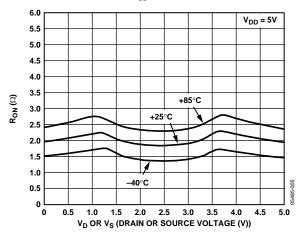


Figure 5. On Resistance as a Function of  $V_{\rm D}$  (Vs) for Different Temperatures  $V_{\rm DD}$  = 5 V

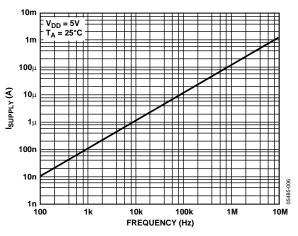


Figure 6. Supply Current vs. Input Switching Frequency

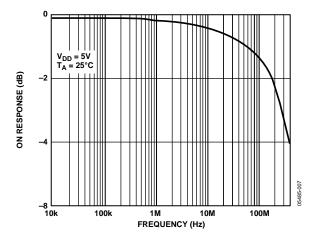


Figure 7. Bandwidth

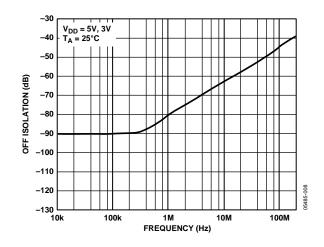
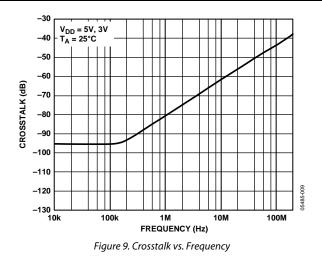
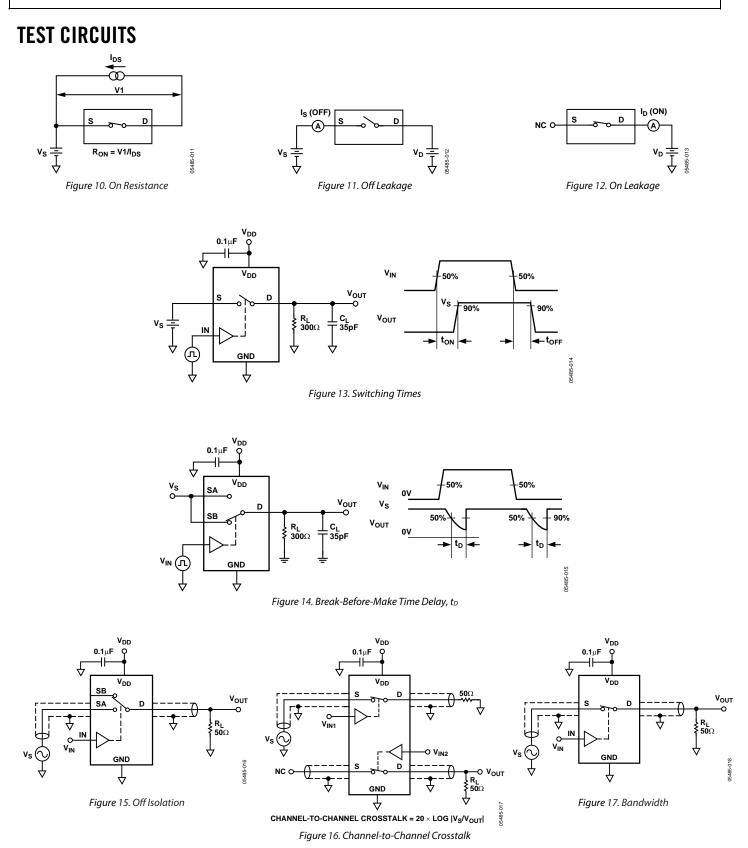


Figure 8. Off Isolation vs. Frequency





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### TERMINOLOGY

#### Ron

Ohmic resistance between D and S.

### $\Delta R_{ON}$

On resistance match between any two channels, such as  $R_{\rm ON}$  maximum –  $R_{\rm ON}$  minimum.

### $R_{\rm FLAT\,(ON)}$

Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.

Is (OFF) Source leakage current with the switch off.

 $I_D$ ,  $I_S$  (ON) Channel leakage current with the switch on.

 $\mathbf{V}_{\mathrm{D}}\left(\mathbf{V}_{S}\right)$  Analog voltage on Terminal D and Terminal S.

Cs (OFF) Off switch source capacitance.

### C<sub>D</sub>, C<sub>S</sub> (ON) On switch capacitance.

### ton

Delay between applying the digital control input and the output switching on (see Figure 13).

### toff

Delay between applying the digital control input and the output switching off.

### t<sub>D</sub>

Off time or on time measured between the 90% points of both switches, when switching from one address state to another (see Figure 14).

### Crosstalk

A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

### **Off Isolation**

A measure of unwanted signal coupling through an off switch.

### Bandwidth

The frequency at which the output is attenuated by -3 dB.

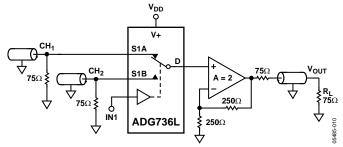
### On Response

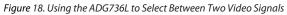
The frequency response of the on switch.

### On Loss

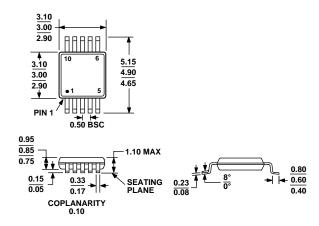
The voltage drop across the on switch, seen on the On Response vs. Frequency plot (see Figure 7) as how many decibels the signal is away from 0 dB at very low frequencies.

## **APPLICATIONS INFORMATION**





### **OUTLINE DIMENSIONS**



COMPLIANT TO JEDEC STANDARDS MO-187-BA

Figure 19. 10-Lead Mini Small Outline Package [MSOP] (RM-10) Dimensions shown in millimeters

### **ORDERING GUIDE**

Model	Temperature Range	Package Description	Package Option	Branding
ADG736LBRM	-40°C to +85°C	10-Lead Mini Small Outline Package (MSOP)	RM-10	SOY
ADG736LBRM-REEL	-40°C to +85°C	10-Lead Mini Small Outline Package (MSOP)	RM-10	SOY
ADG736LBRM-REEL7	-40°C to +85°C	10-Lead Mini Small Outline Package (MSOP)	RM-10	SOY
ADG736LBRMZ <sup>1</sup>	-40°C to +85°C	10-Lead Mini Small Outline Package (MSOP)	RM-10	SOZ
ADG736LBRMZ-REEL <sup>1</sup>	-40°C to +85°C	10-Lead Mini Small Outline Package (MSOP)	RM-10	SOZ
ADG736LBRMZ-REEL71	-40°C to +85°C	10-Lead Mini Small Outline Package (MSOP)	RM-10	SOZ

 $^{1}$  Z = Pb-free part.

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